

2N7002

**SURFACE MOUNT SILICON  
N-CHANNEL  
ENHANCEMENT-MODE  
MOSFET**



**SOT-23 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N7002 type is an N-Channel enhancement-mode MOSFET manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications.

**MARKING CODE: 702**

**MAXIMUM RATINGS:** (T<sub>A</sub>=25°C)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current (T <sub>C</sub> =25°C)
Continuous Drain Current (T <sub>C</sub> =100°C)
Continuous Source Current (Body Diode)
Maximum Pulsed Drain Current
Maximum Pulsed Source Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V <sub>DS</sub>	60	V
V <sub>DG</sub>	60	V
V <sub>GS</sub>	40	V
I <sub>D</sub>	115	mA
I <sub>D</sub>	75	mA
I <sub>S</sub>	115	mA
I <sub>DM</sub>	800	mA
I <sub>SM</sub>	800	mA
P <sub>D</sub>	350	mW
T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
θ <sub>JA</sub>	357	°C/W

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>GSSF</sub>	V <sub>GS</sub> =20V			100	nA
I <sub>GSSR</sub>	V <sub>GS</sub> =20V			100	nA
I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			1.0	μA
I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0, T <sub>A</sub> =125°C			500	μA
I <sub>D(ON)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V	500			mA
BV <sub>DSS</sub>	I <sub>D</sub> =10μA	60	105		V
V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	2.1	2.5	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			3.75	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> =5.0V, I <sub>D</sub> =50mA			0.375	V
V <sub>SD</sub>	V <sub>GS</sub> =0, I <sub>S</sub> =11.5mA			1.5	V
r <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA		3.7	7.5	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA, T <sub>A</sub> =100°C			13.5	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =5.0V, I <sub>D</sub> =50mA		6.2	7.5	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =5.0V, I <sub>D</sub> =50mA, T <sub>A</sub> =100°C			13.5	Ω
g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA	80			mS

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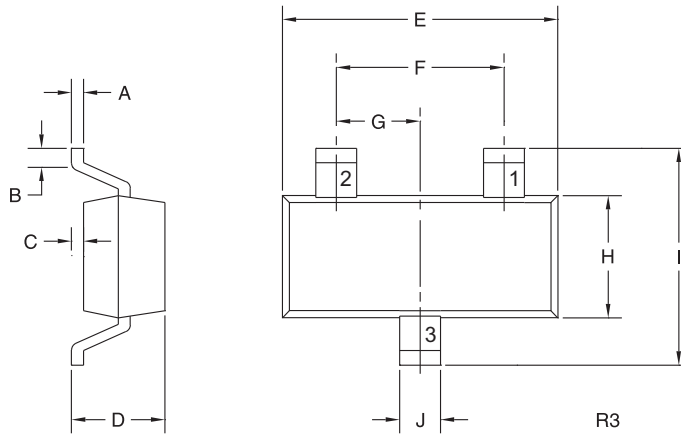
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**ELECTRICAL CHARACTERISTICS - Continued:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
$C_{rss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		5.0	pF
$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50	pF
$C_{oss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		25	pF
$Q_{g(\text{tot})}$	$V_{DS}=30\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$	0.592		nC
$Q_{gs}$	$V_{DS}=30\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$	0.196		nC
$Q_{gd}$	$V_{DS}=30\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$	0.148		nC
$t_{on}$	$V_{DD}=30\text{V}, I_D=200\text{mA}, R_G=25\Omega, R_L=150\Omega$		20	ns
$t_{off}$	$V_{DD}=30\text{V}, I_D=200\text{mA}, R_G=25\Omega, R_L=150\Omega$		20	ns

**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Gate
- 2) Source
- 3) Drain

**MARKING CODE: 702**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

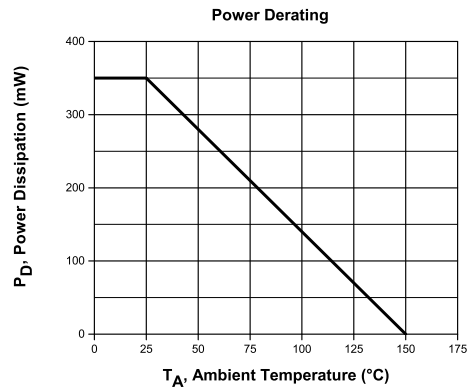
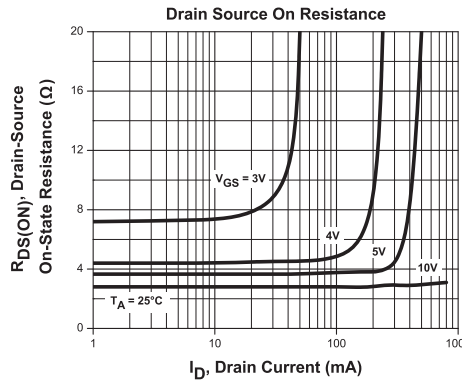
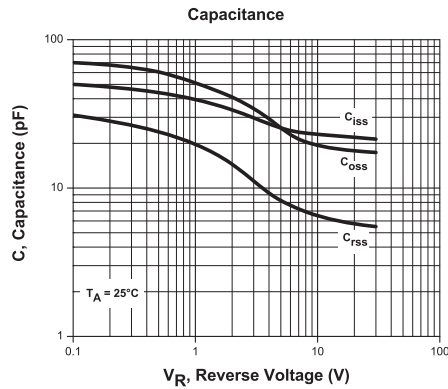
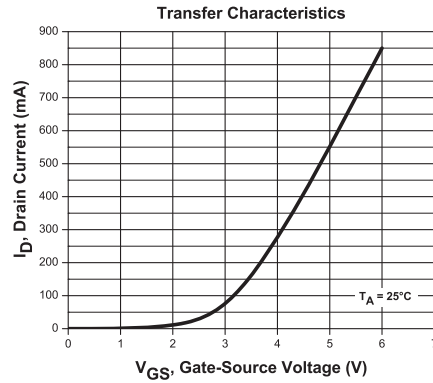
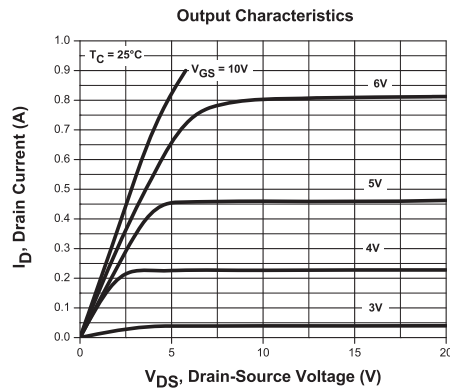
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### TYPICAL ELECTRICAL CHARACTERISTICS



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## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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